Title (en)

STRUCTURED SEMICONDUCTOR ELEMENT FOR REDUCING CHARGING EFFECTS

Title (de)

STRUKTURIERTES HALBLEITERELEMENT ZUR REDUZIERUNG VON CHARGINGEFFEKTEN

Title (fr)

ELEMENT A SEMI-CONDUCTEUR STRUCTURE POUR REDUIRE DES EFFETS DE CHARGE

Publication

EP 1636844 A2 20060322 (DE)

Application

EP 04741625 A 20040521

Priority

- EP 2004050884 W 20040521
- DE 10328007 A 20030621

Abstract (en)

[origin: WO2004114406A3] The invention relates to a semiconductor circuit element (1) for reducing undesirable charging effects, in particular a connection element of test structures for semiconductor circuits. The surface (4) of said semiconductor element (1) comprises printed conductors (3) that are electrically insulated from the remainder of the surface (5) of the semiconductor element (1). In said element, only the printed conductors (3) are connected to semiconductor circuit elements (8) that are situated downstream.

IPC 1-7

H01L 23/58; H01L 23/482; H01L 23/485

IPC 8 full level

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CPC (source: EP US)

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C-Set (source: EP US)

H01L 2224/05624 + H01L 2924/00014

Citation (search report)

See references of WO 2004114406A2

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US 2002079584 A1 20020627 - MATSUNAGA NORIAKI [JP]

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DOCDB simple family (publication)

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